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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/698,551		11/03/2003	Kyo Ho Moon	049128-5048-02	9943	
9629	7590	04/02/2004		EXAMINER		
	-	& BOCKIUS LLP	TON, MINH TOAN T			
WASHING		IA AVENUE NW 20004		ART UNIT	PAPER NUMBER	
	•			2871	-	

DATE MAILED: 04/02/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

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	L Application No.	Applicant/a)	m
	Application No.	Applicant(s)	
	10/698,551	MOON ET AL.	
Office Action Summary	Office Action Summary Examiner Art Unit		
	Toan Ton	2871	
The MAILING DATE of this communication Period for Reply	appears on the cover sheet w	vith the correspondence address	
A SHORTENED STATUTORY PERIOD FOR REI THE MAILING DATE OF THIS COMMUNICATIO - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by sta Any reply received by the Office later than three months after the may earned patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no event, however, may a reply within the statutory minimum of thi tod will apply and will expire SIX (6) MO tute, cause the application to become A	reply be timely filed rly (30) days will be considered timely. NTHS from the mailing date of this communication BANDONED (35 U.S.C. § 133).	on.
Status			
1) Responsive to communication(s) filed on			
, —	his action is non-final.		
3) Since this application is in condition for allow	wance except for formal mat	ters, prosecution as to the merits i	is
closed in accordance with the practice unde	er <i>Ex parte Quayle</i> , 1935 C.I	D. 11, 453 O.G. 213.	
Disposition of Claims			
4)⊠ Claim(s) 10-18 is/are pending in the applica	ition.		
4a) Of the above claim(s) is/are without	Irawn from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>10-18</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and	d/or election requirement.		
Application Papers			-
9) The specification is objected to by the Exam	iner.		
10) The drawing(s) filed on is/are: a) a	accepted or b) objected to	by the Examiner.	
Applicant may not request that any objection to t	he drawing(s) be held in abeya	nce. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the corr	ection is required if the drawing	g(s) is objected to. See 37 CFR 1.121((d).
11) The oath or declaration is objected to by the	Examiner. Note the attache	d Office Action or form PTO-152.	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of:	ign priority under 35 U.S.C.	§ 119(a)-(d) or (f).	
1.☐ Certified copies of the priority docume	ents have been received.		
2. Certified copies of the priority docume		Application No.	
3.☐ Copies of the certified copies of the p			
application from the International Bur	•		
* See the attached detailed Office action for a		received.	
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Attachment(s)			
· ·			

U.S. Patent and Trademark Office PTOL-326 (Rev. 1-04)

1) Notice of References Cited (PTO-892)

Paper No(s)/Mail Date _

2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)

4) Interview Summary (PTO-413)

Paper No(s)/Mail Date. __

6) Other: _

☐ Notice of Informal Patent Application (PTO-152)

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Double Patenting

The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

2. Claims 10-18 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-17 of U.S. Patent No. 6683668. Although the conflicting claims are not identical, they are not patentably distinct from each other because the present claims are broader in scope than the patented claims, i.e., the patent claims anticipates the present claims.

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The patented claim 1 recites: an organic insulating film formed on the substrate; an alignment film having a first etch rate formed on the organic insulating film; and a silicon nitride layer having a second etch rate formed between the alignment film and the organic insulating film, wherein the first etch rate is different from the second etch rate.

The patented claim 2 recites: the alignment film is eliminated by dry-etching during rework processing.

The patented claim 3 recites: the dry-etching is carried out by using at least one compound gas of SF₆, O₂, O₂+Cl₂, and CF₄.

The patented claim 4 recites: a ratio of the compound gas is at least about SF₆:O₂=1:50.

The patented claim 5 recites: a ratio of the compound gas is at least about $SF_6:O_2=1:70$.

The patented claim 6 recites: the dry-etching uses a radio frequency power of about 500-1500W.

The patented claim 7 recites: a gate line on the substrate; a data line crossing the gate line; a gate electrode connected to the gate line; a gate insulating film covering the gate electrode and the gate line; a semiconductor layer formed on the gate insulating film; a source electrode connected to the data line; and a drain electrode formed away from the source electrode with a channel of a fixed size formed therebetween.

The patented claim 9 recites: a pixel electrode electrically contacts the drain electrode and overlaps at least one of the data line and the gate line.

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Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Contact Information

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Toan Ton whose telephone number is (571) 272-2303.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

March 3, 2004

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